

isc N-Channel MOSFET Transistor

2SK791

DESCRIPTION

- Drain Current  $-I_D=3A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}=850V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

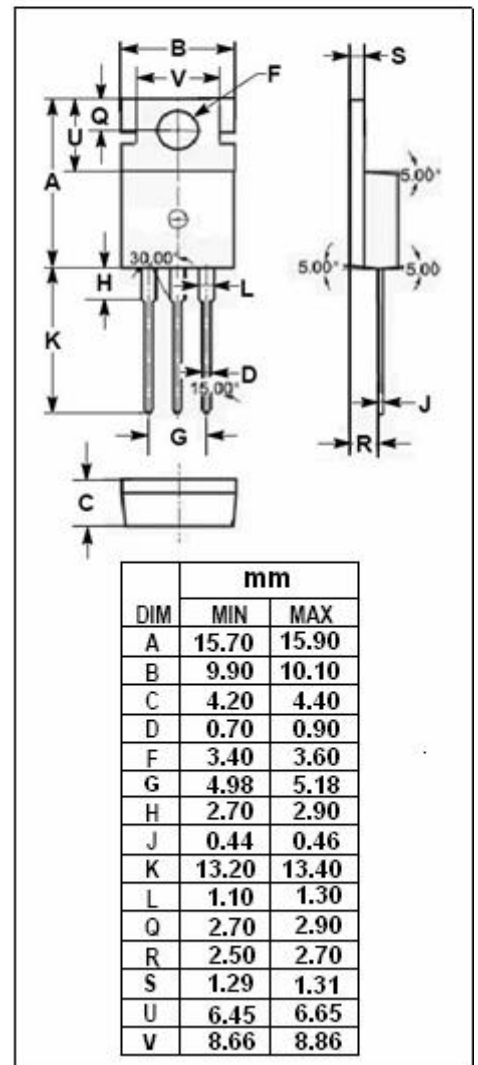
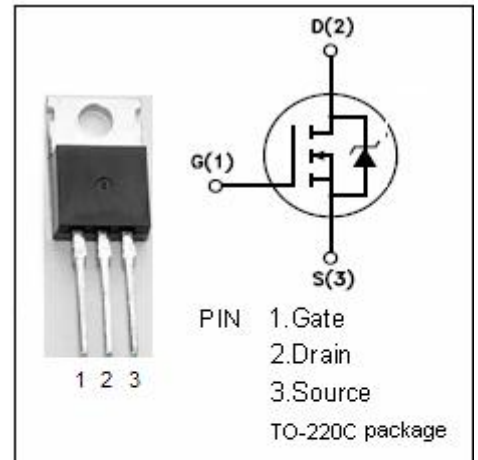
- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	850	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	3	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	100	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.0	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ C/W$



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• ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=10\text{mA}$	850			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10 V_{GS}; I_D=1\text{mA}$	1.5		3.5	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}; I_D=1.5\text{A}$		3.3	4.5	$\Omega$
$I_{GSS}$	Gate Source Leakage Current	$V_{GS}= \pm 20\text{V}; V_{DS}= 0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=850\text{V}; V_{GS}= 0$			300	$\mu\text{A}$
$t_r$	Rise time	$V_{GS}=10\text{V}; I_D=1.5\text{A};$ $R_L=133\ \Omega$		55	120	ns
$t_{on}$	Turn-on time			70	165	ns
$t_f$	Fall time			60	120	ns
$t_{off}$	Turn-off time			280	550	ns